

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☑ Surface-mounted package
- ☑ Low Thermal Resistance

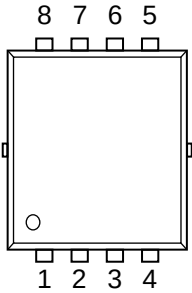
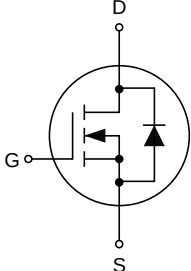
1.2 Applications

- ☑ Motor driver appliances
- ☑ High power inverter system
- ☑ Adapter appliances

1.3 Quick reference

- ☑ $BV \geq 100\text{ V}$
- ☑ $R_{DS(ON)} \leq 9.5\text{ m}\Omega @V_{GS} = 10\text{ V}$
- ☑ $P_D \leq 67\text{ W}$
- ☑ $R_{DS(ON)} \leq 13.5\text{ m}\Omega @V_{GS} = 4.5\text{ V}$
- ☑ $I_D \leq 64\text{ A}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1,2,3	Source	 Top View PDFN3.3x3.3-8L	
4	Gate		
5,6,7,8	Drain		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C=25^{\circ}\text{C}$	100	-	V
V_{GS}	Gate-Source Voltage	$T_C=25^{\circ}\text{C}$	-	± 20	V
$I_D^{*,***}$	Drain Current (DC)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	64	A
		$T_C=100^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	40	A
I_{DM}^{*}	Pulsed Source Current	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	256	A
P_D	Power Dissipation	$T_C=25^{\circ}\text{C}$	-	67	W
E_{AS}^{*}	Single Pulsed Avalanche Energy	$V_{DD}=50\text{ V}, L=0.5\text{ mH}$	-	392	mJ
T_J, T_{stg}	Operating Junction and Storage Temperature Range		-55	150	$^{\circ}\text{C}$
$R_{\theta JA}^{**}$	Thermal Resistance-Junction to Ambient		-	56	$^{\circ}\text{C/W}$
$R_{\theta JC}$	Thermal Resistance-Junction to Case		-	1.85	

Notes:

- * Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- ** Surface mounted on 1 in^2 pad area, $t \leq 10\text{ sec}$.
- *** Limited by bonding wire.

4. Marking Information

Product Name	Marking
KJ0910QM	0910QM XXXXXX

5. Ordering Code

Product Name	Package	Reel size	Tape width	Quantity (pcs)
KJ0910QM	PDFN 3.3x3.3-8L	13"	12 mm	5000

Note: KUAIJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C).

6. Electrical Characteristics (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _{DS} =250 μA	100	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250 μA	1.2	1.8	2.6	V
I _{DSS}	Zero Gate Voltage Source Current	V _{DS} =80 V, V _{GS} =0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{DS} =0 V, V _{GS} =±20 V	-	-	±100	nA
R _{DS(ON)} ^a	On-State Resistance	V _{GS} =10 V, I _{DS} =20 A	-	8.5	9.5	mΩ
		V _{GS} =4.5 V, I _{DS} =10 A	-	10.5	13.5	
g _{FS} ^b	Forward Transconductance	V _{GS} =5 V, I _{DS} =10 A	-	30	-	S
R _g	Gate Resistance	f=1 MHz	-	0.6	-	Ω
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =20 A, V _{GS} =0 V	-	0.9	1.3	V
t _{rr}	Reverse Recovery Time	I _{DS} =20 A, V _{GS} =0V dI _{SD} /dt=100 A/μs	-	43	-	ns
Q _{rr}	Reverse Recovery Charge		-	36	-	nC
Dynamic Characteristics ^b						
C _{iss}	Input Capacitance	V _{GS} =0 V, V _{DS} =50 V Frequency=1 MHz	-	1644	-	pF
C _{oss}	Output Capacitance		-	359	-	
C _{rss}	Reverse Transfer Capacitance		-	13.5	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} =50 V, V _{GEN} =10 V, R _G =3 Ω, I _{DS} =20 A	-	17	-	ns
t _r	Turn-on Rise Time		-	1	-	
t _{d(off)}	Turn-off Delay Time		-	43	-	
t _f	Turn-off Fall Time		-	8.2	-	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =50 V, V _{GS} =10 V, I _{DS} =30 A	-	29	-	nC
Q _{gs}	Gate-Source Charge		-	5.6	-	
Q _{gd}	Gate-Drain Charge		-	6.5	-	

Notes:

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

7. Typical Characteristics

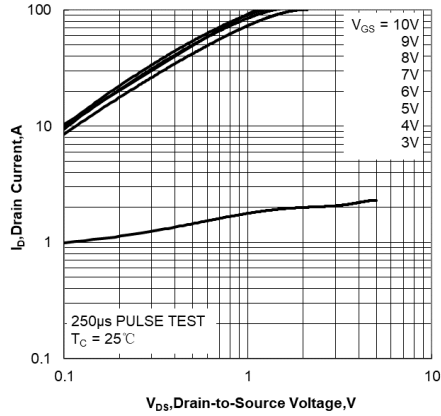


Figure 1. Output Characteristics

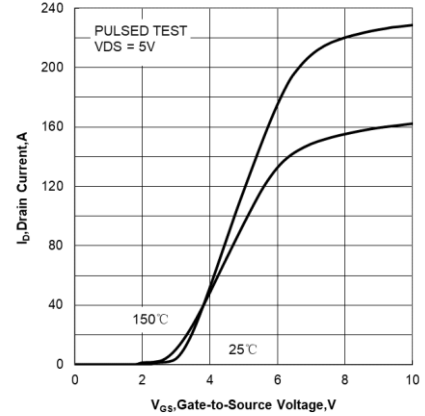


Figure 2. Transfer Characteristics

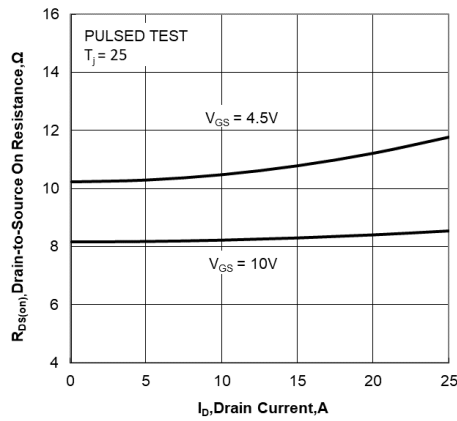


Figure 3. Drain-to-Source On Resistance vs Drain Current

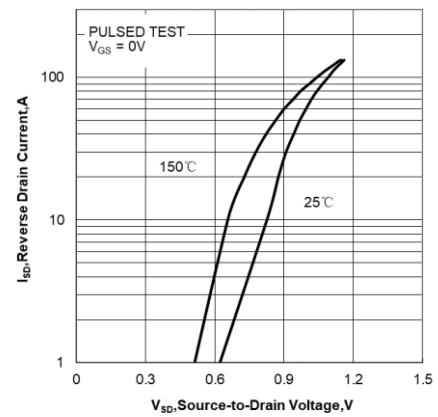


Figure 4. Body Diode Forward Voltage vs Source Current and Temperature

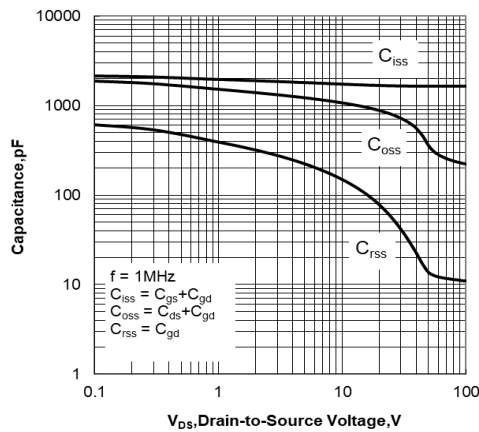


Figure 5. Capacitance Characteristics

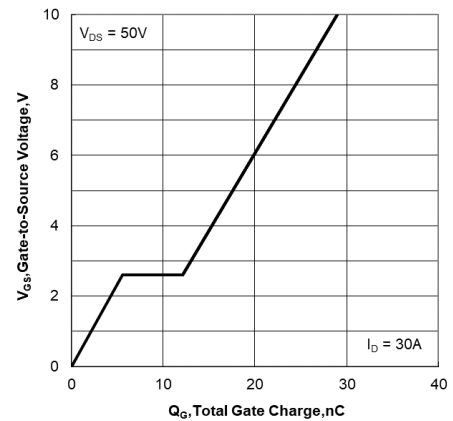


Figure 6. Gate Charge Characteristics

7. Typical Characteristics (cont.)

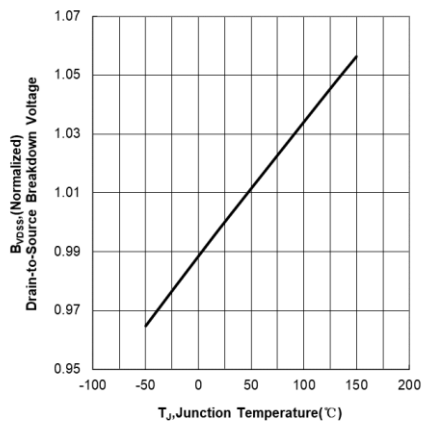


Figure 7. Normalized Breakdown Voltage vs Junction Temperature

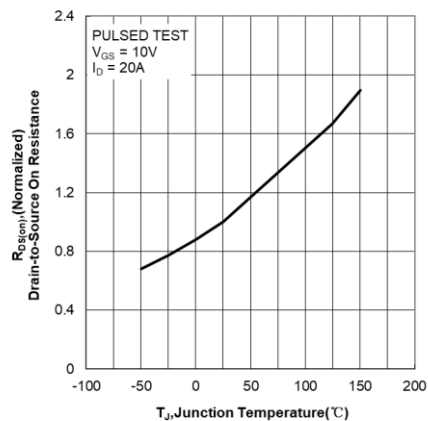


Figure 8. Normalized On Resistance vs Junction Temperature

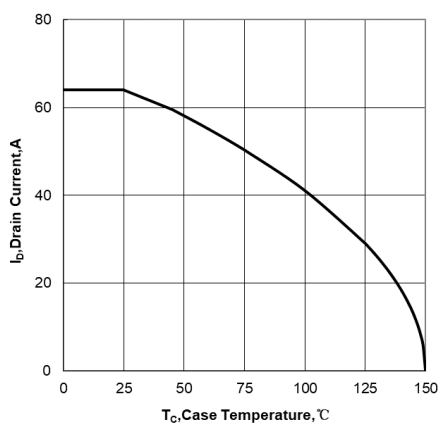


Figure 9. Maximum Continuous Drain Current vs Case Temperature

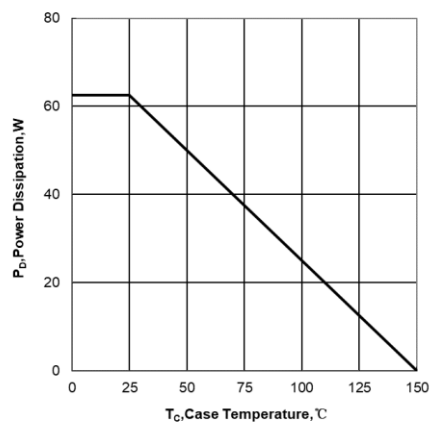


Figure 10. Maximum Power Dissipation vs Case Temperature

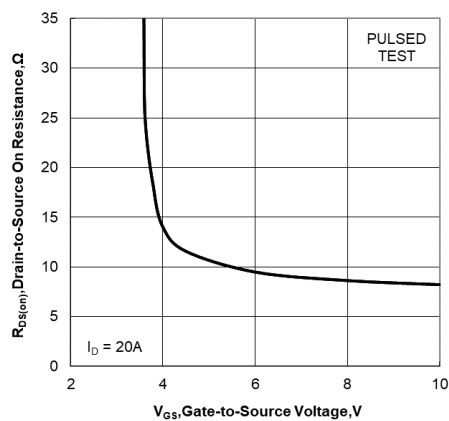


Figure 11. Drain-to-Source On Resistance vs Gate Voltage and Drain Current

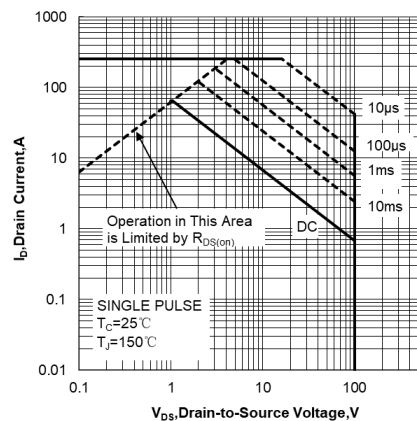


Figure 12. Maximum Safe Operating Area

7. Typical Characteristics (cont.)

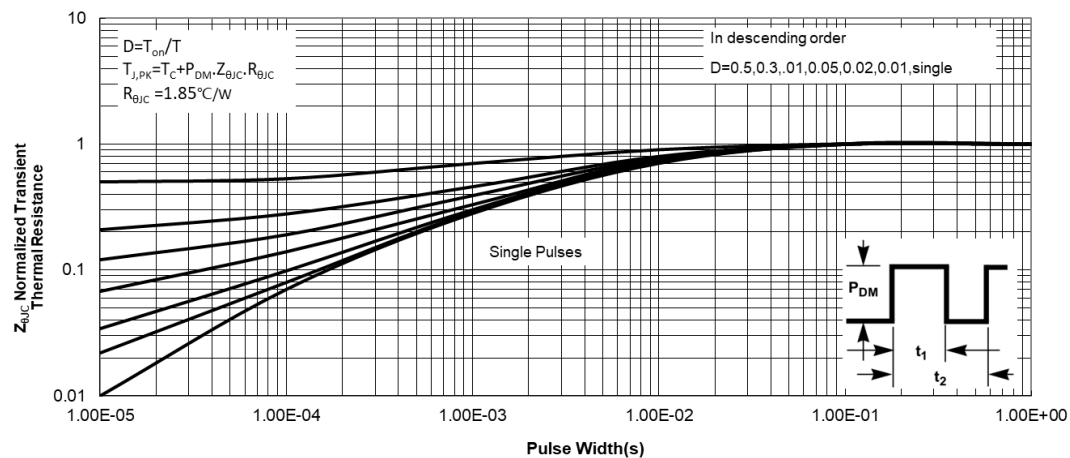
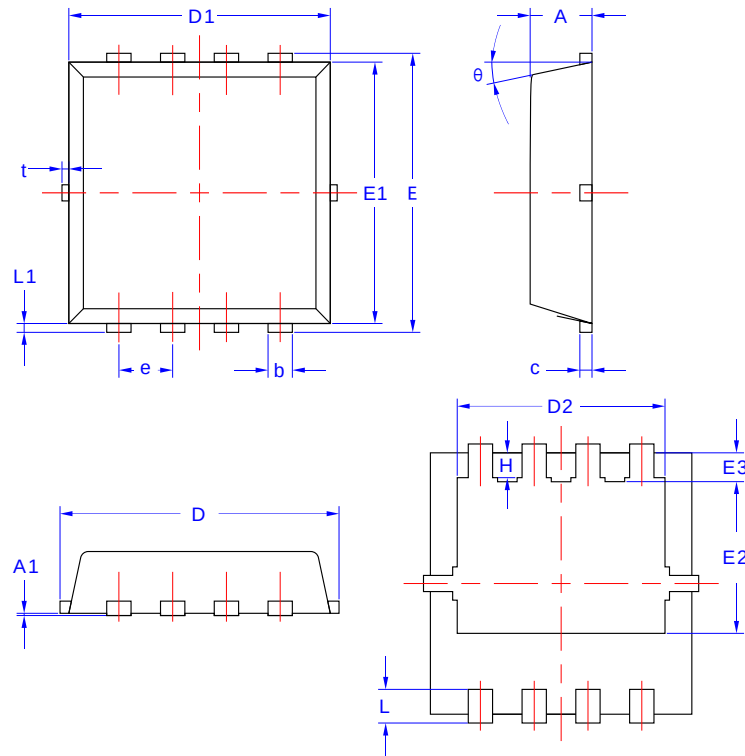


Figure 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

8. Package Dimensions

PDFN 3.3x3.3-8L Package



Symbol	Dimensions in Millimeters	
	MIN	MAX
A	0.65	0.85
A1	/	0.05
b	0.20	0.40
c	0.10	0.25
D	3.15	3.45
D1	2.90	3.10
D2	2.30	2.60
E	3.15	3.45
E1	2.90	3.20
E2	1.54	1.94
E3	0.18	0.48
e	0.55	0.75
L	0.30	0.50
L1	0.06	0.20
H	0.31	0.52
t	0.00	0.13
θ	/	12°